**FGX** 《风光欣》技术资料

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# 2SC2458

**NPN EPITAXIAL SILICON TRANSISTOR**

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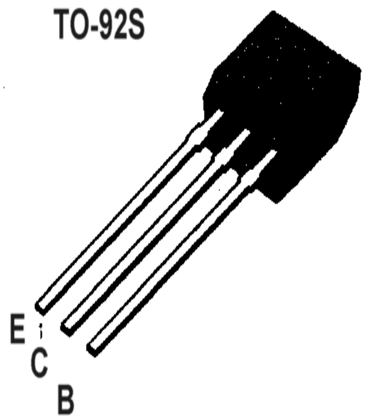
## ABSOLUTE MAXIMUM RATINGS(TA=25 ℃)

| Parameter | Symbol | Limits | Unit |
|---|---|---|---|
| Collector-Base Voltage | $V_{CBO}$ | 50 | V |
| Collector-Emitter Voltage | $V_{CEO}$ | 50 | V |
| Emitter -Base Voltage | $V_{EBO}$ | 5 | V |
| Collector Current | Ic | 150 | mA |
| Collector Dissipation | Pc | 200 | mW |
| Junction Temperature | $T_J$ | 150 | ℃ |
| Storage Temperature | $T_{STG}$ | -55 ~ +150 | ℃ |



## ELECTRCAL CHARACTERISTICS($T_A$=25 ℃)

| Parameter | Symbol | Test Conditions | Min | Typ | Max | Unit |
|---|---|---|---|---|---|---|
| Collector-Base Breakdown Voltage | $BV_{CBO}$ | $I_C$= 0.1mA,$I_E$=0 | 50 | | | V |
| Collector-Emitter Breakdown Voltage | $BV_{CEO}$ | $I_C$= 1mA,$I_B$=0 | 50 | | | V |
| Emitter -Base Breakdown Voltage | $BV_{EBO}$ | $I_E$= 0.1mA,$I_C$=0 | 5 | | | V |
| Collector Cut-off Current | $I_{CBO}$ | $V_{CB}$ =50V,$I_E$=0 | | | 100 | nA |
| Emitter Cut-off Current | $I_{EBO}$ | $V_{EB}$ = 5V,$I_C$=0, | | | 100 | nA |
| Collector-Emitter Saturation Voltage | $V_{CE}$(sat) | $I_C$= 100mA,$I_B$=10mA | | 0.1 | 0.25 | V |
| DC Current Gain | $h_{FE}$ | $V_{CE}$= 6V,$I_C$=2mA, | 70 | | 700 | |
| Transition ftequency | $f_T$ | $V_{CE}$ = 10V,Ic= 1mA | 80 | | | MHZ |
| Output Capacitance | $C_{OB}$ | $V_{CB}$= 10V,$I_E$= 0,f=1MHZ | | 2 | 3.5 | pF |

## $h_{FE}$ CLASSIFICAT ION

| Ltem | O | Y | GR | BL |
|---|---|---|---|---|
| $H_{FE}$ | 70-140 | 120-240 | 200-400 | 350-700 |